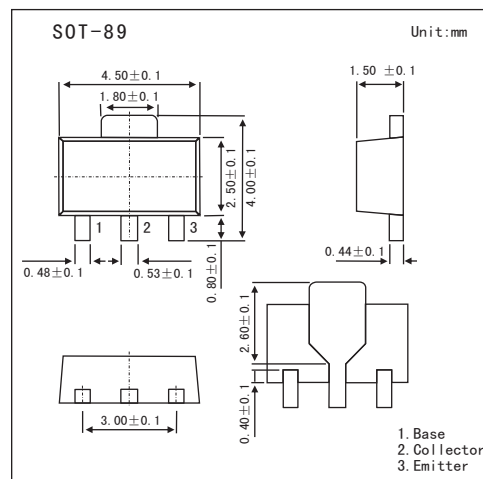


PNP General Purpose Transistors

KTA1662

■ Features

- Small Flat Package.
- Complementary to KTC4374.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.4	A
Collector power dissipation	P_C	500	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}, I_E = 0$	-80			
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5			
Collector cut-off current	I_{CBO}	$V_{CB} = -80\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -50\text{mA}$	70		240	
		$V_{CE} = -2\text{V}, I_C = -200\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -200\text{mA}, I_B = -20\text{mA}$			-0.4	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2\text{V}, I_C = -5\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -10\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		14		

■ h_{FE} Classification

Marking	FO	FY
Rank	O	Y
Range	70~140	120~240